Contents

Quantum Wells

Systematic blue shift of exciton luminescence in strained $Si_{1-x}Ge_x$/Si quantum well structures grown by gas source silicon molecular beam epitaxy 1
S. Fukatsu, H. Yoshida, N. Usami, A. Fujiwara, Y. Takahashi, Y. Shiraki and R. Ito (Tokyo, Japan)

Photoluminescence of SiGe/Si quantum wells prepared by LPCVD 5
L. Vescan, K. Schmidt, C. Dieker (Jülich, Germany), H. P. Tang (Lausanne, Switzerland), T. Vescan (Aachen, Germany) and H. Lüth (Jülich, Germany)

Photoluminescence of confined excitations in MBE-grown $Si_{1-x}Ge_x$/Si(100) single quantum wells 10
M. Wachter, K. Thonke, R. Sauer, F. Schäffler, H.-J. Herzog and E. Kasper (Ulm, Germany)

Magnetotransport studies of remote doped Si/$Si_{1-x}Ge_x$ heterostructures grown on relaxed SiGe buffer layers 15
D. Többen (Garching, Germany), F. Schäffler (Ulm, Germany), A. Zrenner and G. Abstreiter (Garching, Germany)

Electron intersubband absorption in modulation and well-doped Si/$Si_{1-x}Ge_x$ multiple quantum wells 20
H. Hertle (Garching, Germany), F. Schäffler (Ulm, Germany), A. Zrenner, G. Abstreiter and E. Gornik (Garching, Germany)

Hole transport in $Si_{0.8}Ge_{0.2}$ quantum wells at low temperatures 24
C. J. Emeleus, T. E. Whall, D. W. Smith, R. A. Kubiak, E. H. C. Parker (Coventry, UK) and M. J. Kearney (Wembley, UK)

Band gap luminescence in pseudomorphic $Si_{1-x}Ge_x$ quantum wells grown by molecular beam epitaxy 27
J. Brunner, U. Menczigar, M. Gail, E. Freiss and G. Abstreiter (Garching, Germany)

Growth Methods

The deposition of Si–Ge strained layers from GeH_4, SiH_2Cl_2, SiH_4 and Si_2H_6 30
D. J. Meyer (Tempe, AZ, USA) and T. I. Kamins (Palo Alta, CA, USA)

Chemical vapour deposition of epitaxial SiGe thin films from SiH_4–GeH_4–HCl–H_2 gas mixtures in an atmospheric pressure process 34
H. Kühne, Th. Morgenstern, P. Zaumseil, D. Krüger, E. Bugiel and G. Ritter (Frankfurt, Germany)

Si/SiGe/Si heterostructure growth without interface roughness at high germanium mole fractions by low temperature low pressure chemical vapour deposition 38
R. Schütz, J. Murota, T. Maeda, R. Kircher, K. Yokoo, S. Ono (Sendai, Japan) and H. L. Hartnagel (Darmstadt, Germany)

A comparative study of heavy boron doping in silicon and $Si_{1-x}Ge_x$ layers grown by molecular beam epitaxy 42
M. R. Sardela, Jr., W.-X. Ni, H. Radpisheh and G. V. Hansson (Linköping, Sweden)

Photoluminescence and X-ray diffraction study of highly uniform silicon and Ge_xSi_{1-x} epitaxial layers 46
D. W. Greve, R. Misra, T. E. Schlesinger, G. McLaughlin (Pittsburgh, PA, USA) and M. A. Capano (Dayton, OH, USA)

Low temperature silicon and $Si_{1-x}Ge_x$ epitaxy by rapid thermal chemical vapour deposition using hydrides 52
D. Dutartre, P. Warren, I. Berbezier and P. Perret (Meylan, France)

Crystallization of amorphous Ge_x/Si_{1-x} films on SiO_2 57
F. Eldelman, Y. Komem (Haifa, Israel), S. S. Iyer, (New York, NY, USA), J. Heydenreich and D. Baither (Halle-am-salle, Germany)

Growth and Characterization

Photoluminescence and electrical characterization of SiGe/Si heterostructures grown by rapid thermal chemical vapour deposition ... 60
G. Bremond, A. Souifi, T. Benyattou (Villeurbanne, France) and D. Dutartre (Meylan, France)

Characterization of SiGe multiple quantum wells by spectroscopic ellipsometry and photoluminescence 69
J. Hulse, N. Rowell, J.-P. Noël and S. Rolfe (Ottawa, Ont., Canada)

SiGe materials characterized by high resolution Raman spectroscopy and spectroscopic ellipsometry 73
P. Evrard, J. L. Stehle (Bois-Colombes, France), C. Pickering and R. T. Caline (Malvern, UK)

Evolution of surface morphology and strain during SiGe epitaxy 78
A. J. Pidduck, D. J. Robbins, A. G. Cullis, W. Y. Leong and A. M. Pitt (Malvern, UK)

Photoreflectance study of strained (001) $Si_{1-x}Ge_x$/Si layers 85
Y. Yin, F. H. Pollak (Brooklyn, NY, USA), P. Auvray (Lannion, France), D. Dutartre, R. Pantel and J. A. Chroboczek (Meylan, France)

Band edge and deep level photoluminescence of fully strained $Si_{1-x}Ge_x$/Si alloys 89
J. Denzel, K. Thonke, J. Spitzer, R. Sauer, H. Kibbel, H.-J. Herzog and E. Kasper (Ulm, Germany)

Observation of electroluminescence from pseudomorphic $Si_{1-x}Ge_x$ alloy layers 94
U. Mantz, K. Thonke, R. Sauer, E. Kasper, H. Kibbel, F. Schäffler and H.-J. Herzog (Ulm, Germany)

Surfaces and Interfaces

Atomistic processes of surface segregation during Si–Ge MBE growth 98
D. E. Jesson, S. J. Pennycook (Oak Ridge, TN, USA), J.-M. Baribeau and D. C. Houghton (Ottawa, Ont., Canada)

Germanium segregation induced reconstruction of SiGe layers deposited on Si(100) 104
R. Butz and S. Kampers (Jülich, Germany)

Temperature-dependent growth anisotropy observed on Si(001) surfaces during silicon gas source molecular beam epitaxy using disilane 108
S. M. Mokler, N. Ohtani, J. Zhang and B. A. Joyce (London, UK)

Effect of a surfactant on the growth of Si/Ge heterostructures 112
K. Sakamoto, K. Miki, T. Sakamoto, H. Yamaguchi, H. Oyanagi, H. Matsuhata and K. Kyoya (Tsukuba, Japan)

The electrical assessment of p-isotype Si/SiGe/Si heterostructures grown by MBE 116
J. C. Brighten, R. A. Kubiak, P. J. Phillips, T. E. Whall, E. H. C. Parker (Coventry, UK), I. D. Kawkins and A. R. Peaker (Manchester, UK)

Processing/Devices

Normal incidence hole intersubband quantum well infrared photodetectors in pseudomorphic Ge_xSi_{1-x}/Si 120
R. People, J. C. Bean, S. K. Sputz, C. G. Bethea and L. J. Peticolas (Murray Hill, NJ, USA)

Low-temperature *in situ* cleaning of silicon wafers with an ultra high vacuum compatible plasma source 126
J. Ramm, E. Beck, A. Züger (Balzers, Liechtenstein), A. Dommann (Buchs, Switzerland) and R. E. Pixley (Zürich, Switzerland)

Molecular beam epitaxy grown $Si/Si_{0.87}Ge_{0.13}$ heterojunction bipolar transistors with ideal $I-V$ characteristics 132
D. J. Gravesteijn, A. Pruijmboom, W. J. Kersten, J. M. L. van Rooij-Mulder, A. H. Reader and J. Slotboom (Eindhoven, The Netherlands)

50 GHz $Si_{1-x}Ge_x$ heterobipolar transistor: growth of the complete layer sequence by molecular beam epitaxy 137
E. Kasper, H. Kibbel and A. Gruhle (Ulm, Germany)

A comparison of the behaviour of $Si_{0.5}Ge_{0.5}$ alloy during dry and wet oxidation 141
J. P. Zhang, P. L. F. Hemment (Guildford, UK), S. M. Newstead, A. R. Powell, T. E. Whall and E. H. C. Parker (Coventry, UK)

UV-assisted oxidation of SiGe strained layers 145
V. Craciun (London, UK), A. H. Reader, W. Kersten, J. Timmers, D. J. Gravesteijn (Eindhoven, The Netherlands) and I. W. Boyd (London, UK)

Boron-doped Si/Ge superlattices and heterostructures 150
J. F. Nützel, F. Meier, E. Friess and G. Abstreiter (Garching, Germany)

Electrical characterization of Si–Ge heterostructure bipolar transistors 154
J. Engvall, V. Nagesh, H. G. Grimmeiss (Lund, Sweden), H.-U. Schreiber (Bochum, Germany) and E. Kasper (Ulm, Germany)

Strain relaxation in epitaxial $Si_{1-x}Ge_x/Si(100)$ layers induced by reaction with palladium 157
A. Buxbaum, E. Zolotoyabko, M. Eizenberg (Haifa, Israel) and F. Schäffler (Ulm, Germany)

Strain/Defects

The energy of systems of misfit dislocations in epitaxial strained layers 161
A. Atkinson (Didcot, UK) and S. C. Jain (Leuven, Belgium)

1 MeV electron irratiation induced degradation of boron-doped strained $Si_{1-x}Ge_x$ layers 166
J. Vanhellemont, M.-A. Trauwaert, J. Poortmans, M. Caymax (Leuven, Belgium) and P. Clauws (Gent, Belgium)

Deep level transient spectroscopy study of defects in megaelectronvolt germanium ion implanted silicon 173
C. Jagadish, B. G. Svensson, N. Hauser and J. S. Williams (Canberra, Australia)

Crystallization kinetics of boron- and germanium-implanted ⟨100⟩ Si: a balance between doping and strain effects 176
F. Corni, R. Tonini, G. Ottaviani (Modena, Italy), M. Servidori (Bologna, Italy) and F. Priolo (Catania, Italy)

Stress in $Si_{1-x}Ge_x$ films prepared by ion beam sputtering: origin and relaxation 180
Y. Le Meur, F. Meyer, C. Pellet, C. Schwebel, P. Möller (Paris, France), A. Buxbaum, (Haifa, Israel), A. Raizman (Yavne, Israel) and M. Eizenberg (Haifa, Israel)

Elastic strain energy of graded $Si_{1-x}Ge_x$ buffer layers 184
G. Heigl, G. Span (Leoben, Austria) and E. Kasper (Ulm, Germany)

Experimental study of Si–Ge tetrahedral solid solution in Ni–Co–Mg talcs 189
F. Martin, S. Petit, A. Decarreau, O. Grauby (Poitiers, France), J. L. Hazemann (Grenoble, France) and Y. Noack (Marseille, France)

Porous Silicon

Electroluminescent performance of porous silicon 196
F. Kozlowski, M. Sauter, P. Steiner, A. Richter, H. Sandmaier and W. Lang (Munich, Germany)

Bright visible photoluminescence in thin silicon films 200
T. P. Pearsall, J. C. Adams, J. N. Kidder, Jr., P. S. Williams, S. A. Chambers, J. Lach, D. T. Schwartz and B. Z. Nosho, (Seattle, WA, USA)

Ultrathin Si/Ge Superlattices (Workshop)

Quantitative theory of optical properties of Si–Ge heterostructures 205
M. Jaros, A. W. Beavis, P. J. Hagon, R. J. Turton, A. Miloszewski and K. B. Wong (Newcastle upon Tyne, UK)

Electronic properties of strained Si/Ge superlattices: tight binding approach 209
G. Theodorou, C. Tserbak and H. M. Polatoglou (Thessaloniki, Greece)

Si/Ge superlattice embedded in silicon and germanium: electronic structure and transition probabilities 212
H. M. Polatogou, C. Tserbak and G. Theodorou (Thessaloniki, Greece)

Buffer concepts of ultrathin Si_mGe_n superlattices 215
H. Presting and H. Kibbel (Ulm, Germany)

Characterization of short-period Si_mGe_n superlattices by high-resolution transmission electron microscopy and X-ray diffraction 221
W. Jäger, D. Stenkamp, P. Ehrhart, K. Leifer, W. Sybertz (Jülich, Germany), H. Kibbel, H. Presting and E. Kasper (Ulm, Germany)

Photoluminescence studies of $Si/Si_{1-x}Ge_x$ quantum wells and Si_mGe_n superlattices 227
U. Menczigar, J. Brunner, E. Freiss, M. Gail, G. Abstreiter (Garching, Germany), H. Kibbel, H. Presting and E. Kasper (Ulm, Germany)

Photoluminescence from short-period strained-layer superlattices of $(Si_6Ge_4)_p$ after hydrogen passivation 234
K. Dettmer (Braunschweig, Germany) and J. Weber (Stuttgart, Germany)

Optical and electrical characterization of Si/Ge superlattices 237
H. G. Grimmeiss, V. Nagesh, J. Engvall, J. Olajos (Lund, Sweden), H. Presting, H. Kibbel and E. Kasper (Ulm, Germany)

Band-to-band transitions in strain-symmetrized, short-period Si/Ge superlattices 243
J. Olajos, J. Engvall, H. G. Grimmeiss (Lund, Sweden), H. Kibbel, E. Kasper and H. Presting (Ulm, Germany)

Optical transitions in strained Ge/Si superlattices 246
U. Schmid, J. Humlíček, F. Lukes, M. Cardona (Stuttgart, Germany), H. Presting, H. Kibbel, E. Kasper (Ulm, Germany), K. Eberl, W. Wegscheider and G. Abstreiter (Garching, Germany)

In-plane and vertical high-frequency conductivity in Si/Ge short-period superlattices 251
T. Fromherz, M. Helm, G. Bauer (Linz, Austria), H. Kibbel and E. Kasper (Ulm, Germany)

Differential optical absorption spectroscopy and X-ray characterization of symmetrically strained Ge–Si superlattices 254
T. P. Pearsall, C. C. M. Bitz, L. B. Sorensen (Seattle, WA, USA), H. Presting and E. Kasper (Ulm, Germany)

Ambient pressure scanning tunneling microscope imaging of hydrogen-passivated Si/Ge multilayers 259
T. Pinnington, A. Sanderson, T. Tiedje (Vancouver, BC, Canada), T. P. Pearsall (Seattle, WA, USA), E. Kasper and H. Presting (Ulm, Germany)

Photocapacitance studies of short-period Si/Ge superlattices 265
V. Nagesh, H. G. Grimmeiss (Lund, Sweden), H. Presting, H. Kibbel and E. Kasper (Ulm, Germany)

In-plane Raman scattering of [001]-grown Si/Ge superlattices 269
R. Schorer, W. Wegscheider, K. Eberl (Garching, Germany), E. Kasper, H. Kibbel (Ulm, Germany) and G. Abstreiter (Garching, Germany)

Author Index 274

Subject Index 276